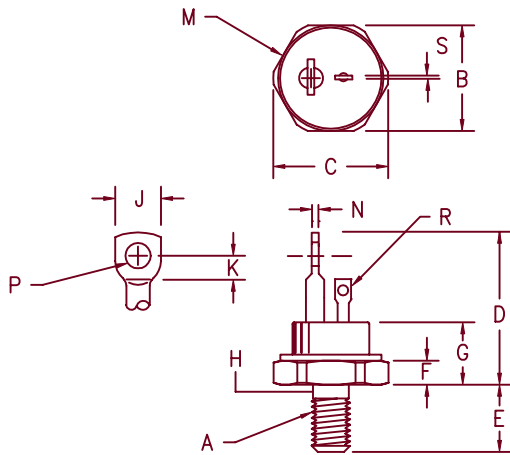


Silicon Controlled Rectifier/Inverter Series 035



Note 1: 1/4-28 UNF-3A

Note 2: Full thread within 2 1/2 threads

Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	---	---	---	---	1
B	.677	.685	17.20	17.40	
C	---	.770	---	19.56	
D	1.200	1.250	30.48	31.75	
E	.427	.447	10.84	11.35	
F	.115	.155	2.92	3.94	
G	---	.515	---	13.08	
H	---	.249	---	6.32	2
J	.200	.300	5.08	7.62	
K	.120	---	3.05	---	
M	---	.667	---	16.94	Dia.
N	.065	.085	1.65	2.15	
P	.145	.155	3.68	3.93	Dia.
R	.055	.065	1.40	1.65	Dia.
S	.025	.030	.64	.76	

TO-208AC (TO-65)

Microsemi
Catalog Number

03508G(2)F
03510G(2)F
03512G(2)F

Note 1: To specify dv/dt other than 200V/usec., enter appropriate letter in place of "G":

K 300V/usec.

H 500V/usec.

J 1000V/usec.

Note 2: To specify tq, enter appropriate letter in (2)

W-30 usec

X-40 usec

Forward & Reverse
Repetitive Blocking
VDRM, VRRM

800V

1000V

1200V

- dv/dt-200 V/usec
- 1000 amperes surge current
- Low forward on-state voltage
- Blocking voltages up to 1200 volts
- Primarily for forced commutated applications

Electrical Characteristics

Max. RMS on-state current

I_{T(RMS)} 63 Amps

T_C = 100°C, half sine wave, R_{θJC} = 0.35°C/W

Max. average on-state cur.

I_{T(AV)} 40 Amps

T_C = 100°C, half sine wave, R_{θJC} = 0.35°C/W

Max. peak on-state voltage

V_{TM} 2.8 Volts

I_{TM} = 120 A(peak)

Max. holding current

I_H 500 mA

Max. peak one cycle surge current

I_{TSM} 800 A

T_C = 100°C, 60Hz

Max. I²t capability for fusing

I²t 2650A²S

t = 8.3 ms

T_C = 25°C unless otherwise noted

Thermal and Mechanical Characteristics

Operating junction temp range

T_J

-65°C to 125°C

Storage temperature range

T_{STG}

-65°C to 150°C

Maximum thermal resistance

R_{θJC}

0.35°C/W Junction to case

Typical thermal resistance (greased)

R_{θCS}

0.20°C/W Case to sink

Mounting torque

25-30 inch pounds

Weight

0.56 ounces (16 grams) typical

3-31-03 Rev. 1

035

Switching

Critical rate of rise of on-state current (note 1)	di/dt	200A/usec.	$T_J = 125^\circ\text{C}$
Typical delay time (note 1)	t_d	2.0 usec.	
Maximum circuit commuted turn-off time (note 2)	$t_q (W)$	30 usec.	$T_J = 125^\circ\text{C}$
	$t_q (X)$	40 usec.	$T_J = 125^\circ\text{C}$

Note 1: $I_{TM} = 50\text{A}$, $V_D = V_{DRM}$, $V_{GT} = 12\text{V}$ open circuit, 20 ohm-0.1 usec. rise time

Note 2: $I_{TM} = 50\text{A}$, $di/dt = -5\text{A/usec.}$, V_R during turn-off interval = 50V min.,
reapplied $dv/dt = 20\text{V/usec.}$, $V_{GT} = 0\text{V}$

Triggering

Max. gate voltage to trigger	V_{GT}	2.0V	$T_J = 25^\circ\text{C}$
Max. nontriggering gate voltage	V_{GD}	0.15V	$T_J = 125^\circ\text{C}$
Max. gate current to trigger	I_{GT}	150mA	$T_J = 25^\circ\text{C}$
Max. peak gate power	P_{GM}	10W	
Average gate power	$P_{G(AV)}$	2.0W	$t_p = 10 \text{ usec.}$
Max. peak gate current	I_{GM}	3.0A	
Max. peak gate voltage (forward)	V_{GM}	20V	
Max. peak gate voltage (reverse)	V_{GM}	10V	

Blocking

Max. leakage current	I_{RRM}, I_{DRM}	20mA	$T_J = 125^\circ\text{C} \ \& \ V_{DRM}, V_{RRM}$
Max. reverse leakage	I_{RRM}, I_{DRM}	500 μA	$T_J = 25^\circ\text{C} \ \& \ V_{RRM}, V_{RRM}$
Critical rate of rise of off-state voltage	dv/dt	200V/usec.	$T_J = 125^\circ\text{C}$

Figure 1
Typical Forward On-State Characteristics

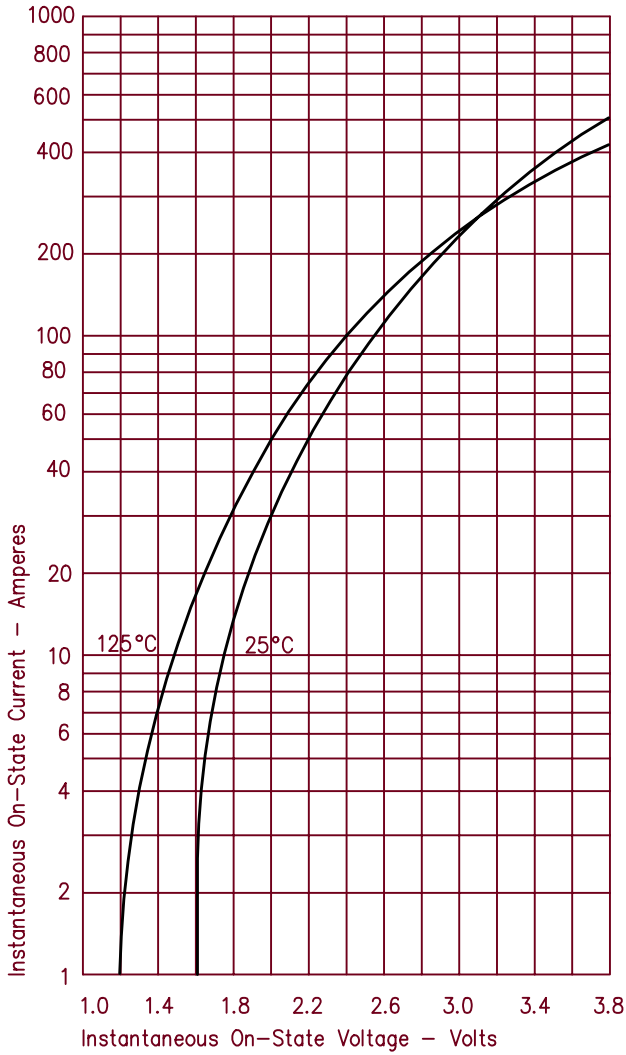


Figure 3
Maximum Power Dissipation

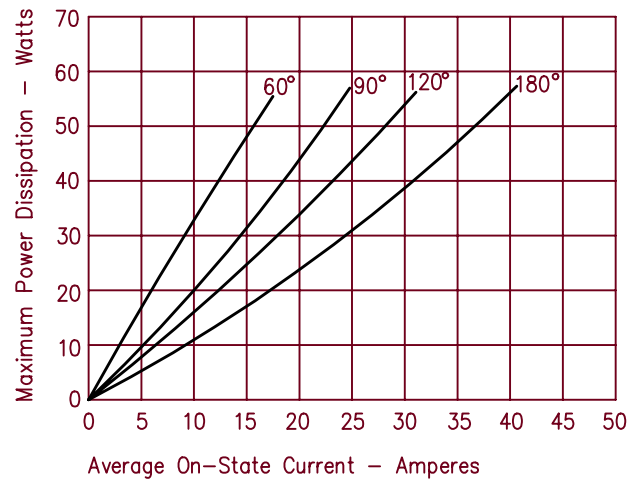


Figure 4
Transient Thermal Impedance

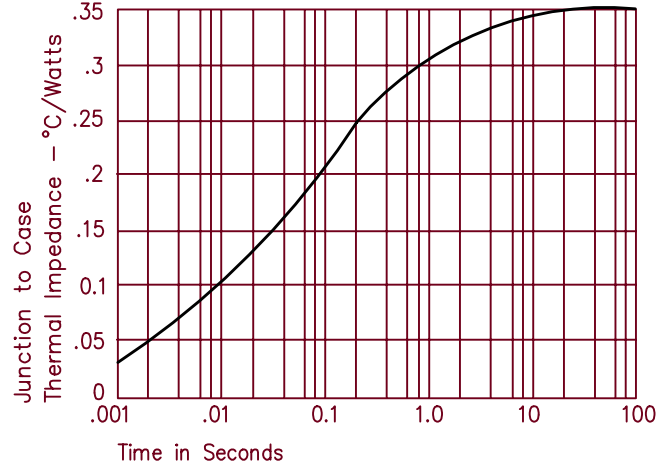


Figure 2
Forward Current Derating

